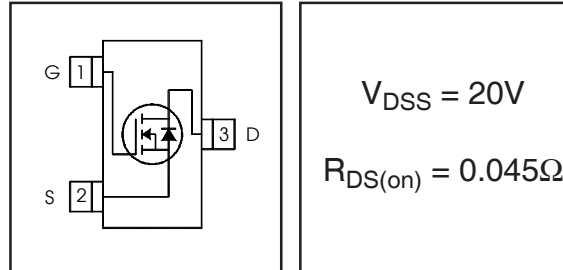


IRLML2502PbF

HEXFET® Power MOSFET

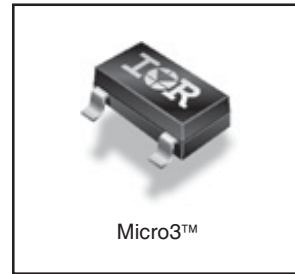
- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free



Description

These N-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|---|--------------|-------|
| V_{DS} | Drain- Source Voltage | 20 | V |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 4.5V$ | 4.2 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 4.5V$ | 3.4 | |
| I_{DM} | Pulsed Drain Current ① | 33 | |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation | 1.25 | W |
| $P_D @ T_A = 70^\circ C$ | Power Dissipation | 0.8 | |
| | Linear Derating Factor | 0.01 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 12 | V |
| T_J, T_{STG} | Junction and Storage Temperature Range | -55 to + 150 | °C |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|------------------------------|------|------|-------|
| $R_{\theta JA}$ | Maximum Junction-to-Ambient③ | 75 | 100 | °C/W |

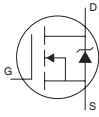
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International
IRF Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|-------|-------|-------|--|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 20 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.01 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 0.035 | 0.045 | Ω | V _{GS} = 4.5V, I _D = 4.2A ② |
| | | — | 0.050 | 0.080 | | V _{GS} = 2.5V, I _D = 3.6A ② |
| V _{GS(th)} | Gate Threshold Voltage | 0.60 | — | 1.2 | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Transconductance | 5.8 | — | — | S | V _{DS} = 10V, I _D = 4.0A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 16V, V _{GS} = 0V |
| | | — | — | 25 | | V _{DS} = 16V, V _{GS} = 0V, T _J = 70°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | -100 | nA | V _{GS} = -12V |
| | Gate-to-Source Reverse Leakage | — | — | 100 | | V _{GS} = 12V |
| Q _g | Total Gate Charge | — | 8.0 | 12 | nC | I _D = 4.0A |
| Q _{gs} | Gate-to-Source Charge | — | 1.8 | 2.7 | | V _{DS} = 10V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 1.7 | 2.6 | | V _{GS} = 5.0V ② |
| t _{d(on)} | Turn-On Delay Time | — | 7.5 | — | ns | V _{DD} = 10V |
| t _r | Rise Time | — | 10 | — | | I _D = 1.0A |
| t _{d(off)} | Turn-Off Delay Time | — | 54 | — | | R _G = 6Ω |
| t _f | Fall Time | — | 26 | — | | R _D = 10Ω ② |
| C _{iss} | Input Capacitance | — | 740 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 90 | — | | V _{DS} = 15V |
| C _{rss} | Reverse Transfer Capacitance | — | 66 | — | | f = 1.0MHz |

Source-Drain Ratings and Characteristics

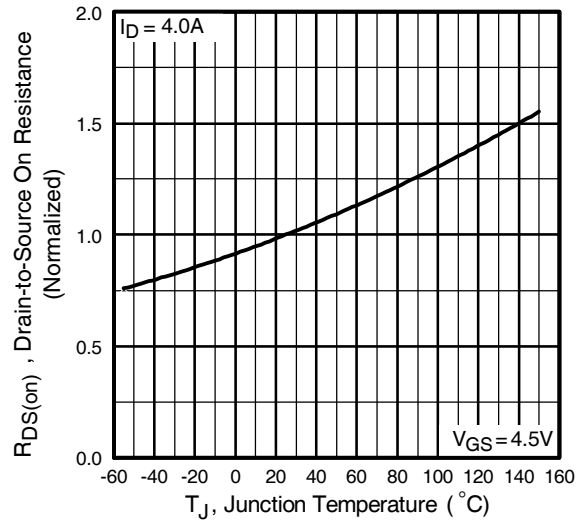
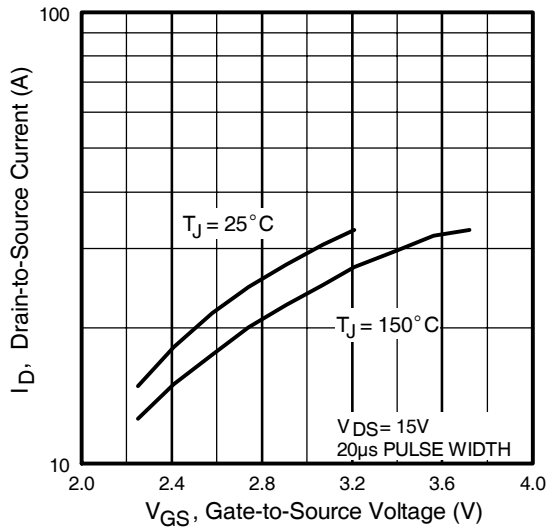
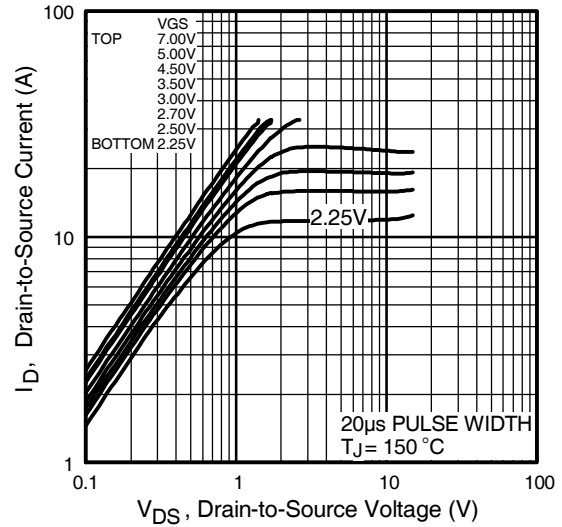
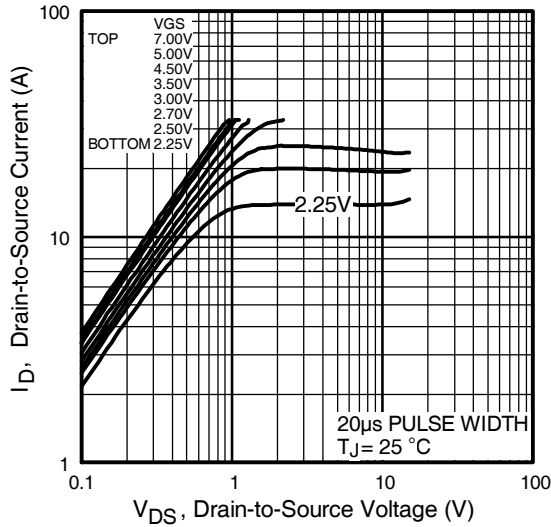
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|--|------|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 1.3 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 33 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.2 | V | T _J = 25°C, I _S = 1.3A, V _{GS} = 0V ② |
| t _{rr} | Reverse Recovery Time | — | 16 | 24 | ns | T _J = 25°C, I _F = 1.3A |
| Q _{rr} | Reverse Recovery Charge | — | 8.6 | 13 | nC | di/dt = 100A/μs ② |

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Pulse width ≤ 300μs; duty cycle ≤ 2%.

③ Surface mounted on FR-4 board, t ≤ 5sec.



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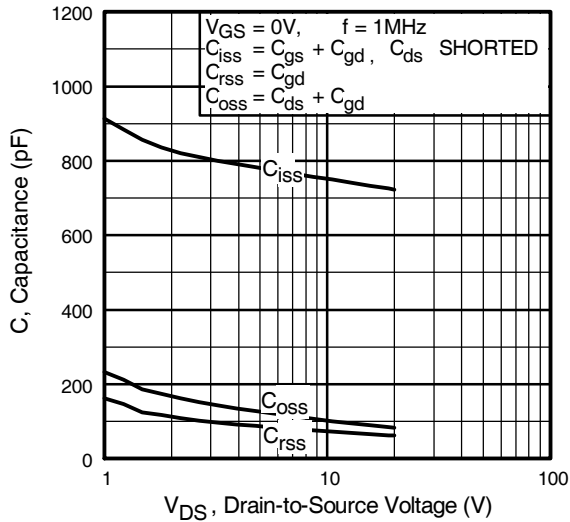


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

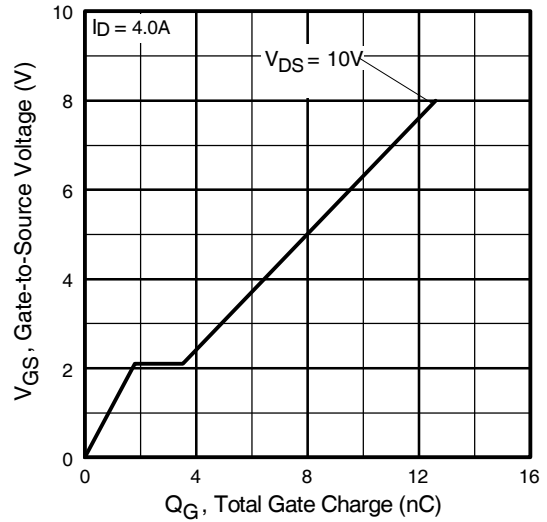


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

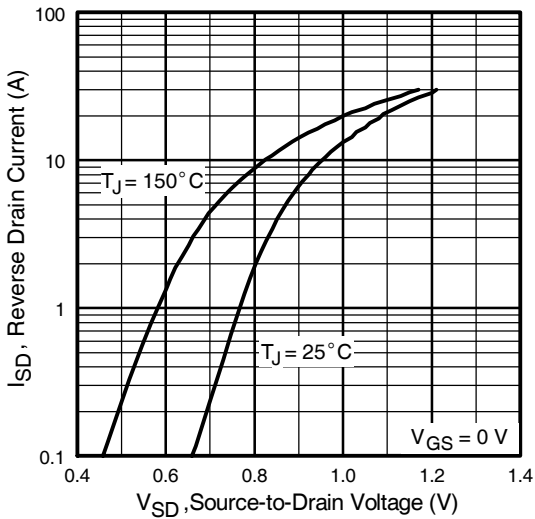


Fig 7. Typical Source-Drain Diode Forward Voltage

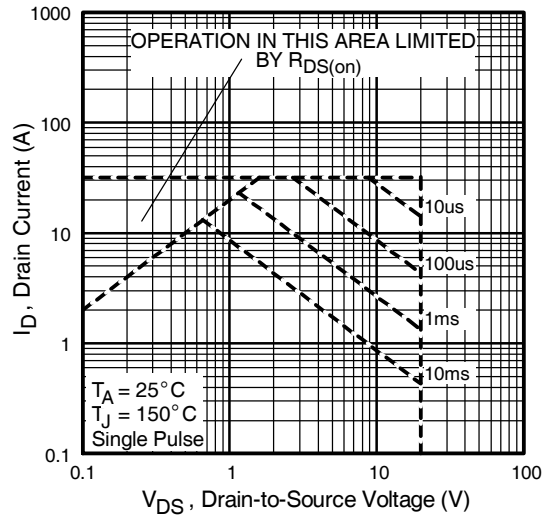


Fig 8. Maximum Safe Operating Area

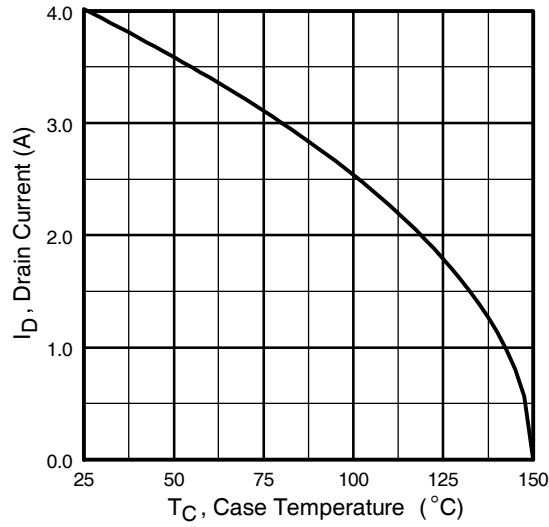


Fig 9. Maximum Drain Current Vs. Case Temperature

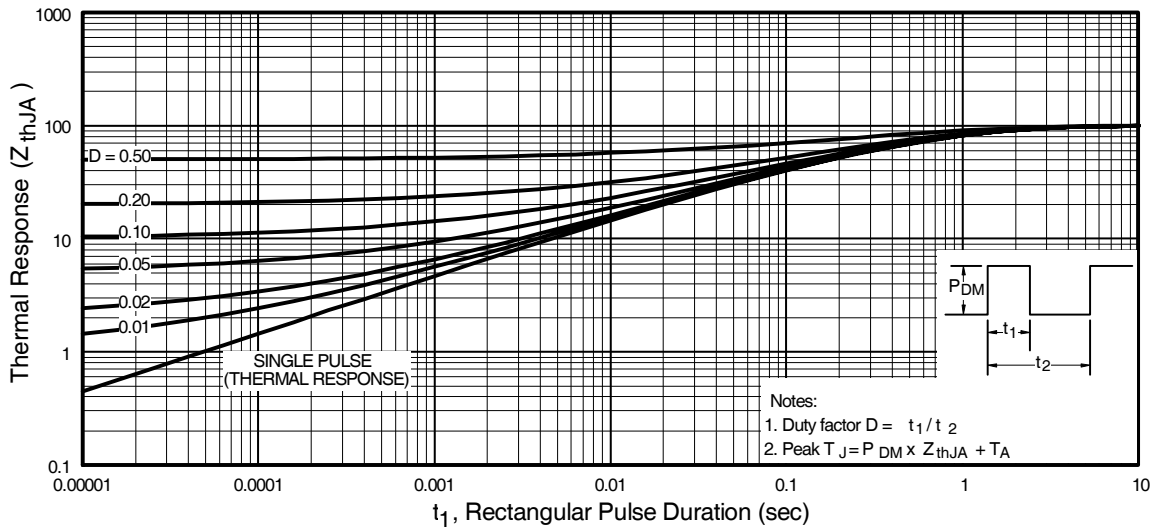


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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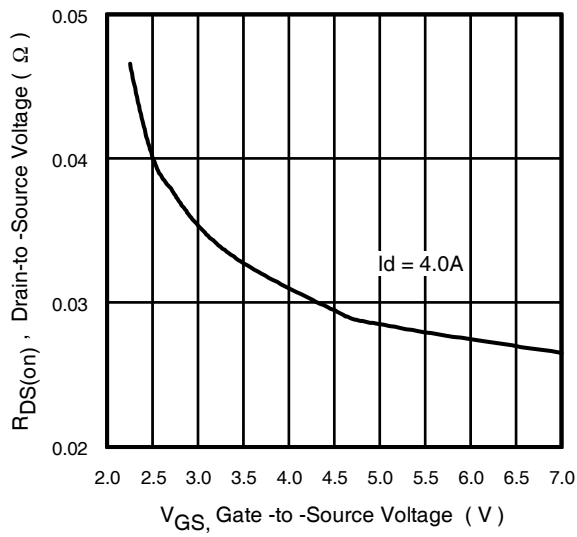


Fig 11. On-Resistance Vs. Gate Voltage

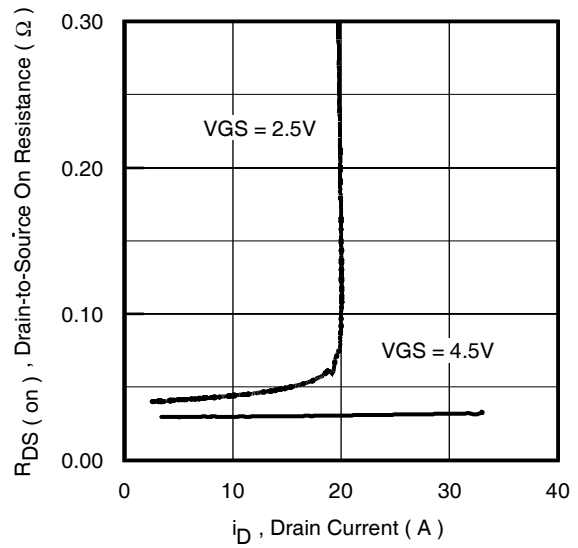
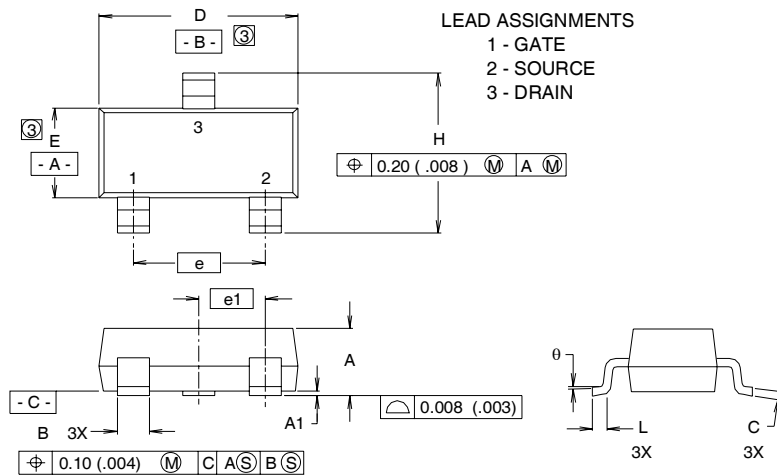


Fig 12. On-Resistance Vs. Drain Current

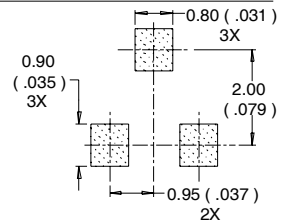
Micro3™ Package Outline

Dimensions are shown in millimeters (inches)



| DIM | INCHES | | MILLIMETERS | |
|-----|-------------|------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .032 | .044 | 0.82 | 1.11 |
| A1 | .001 | .004 | 0.02 | 0.10 |
| B | .015 | .021 | 0.38 | 0.54 |
| C | .004 | .006 | 0.10 | 0.15 |
| D | .105 | .120 | 2.67 | 3.05 |
| e | .0750 BASIC | | 1.90 BASIC | |
| e1 | .0375 BASIC | | 0.95 BASIC | |
| E | .047 | .055 | 1.20 | 1.40 |
| H | .083 | .098 | 2.10 | 2.50 |
| L | .005 | .010 | 0.13 | 0.25 |
| θ | 0° | 8° | 0° | 8° |

MINIMUM RECOMMENDED FOOTPRINT



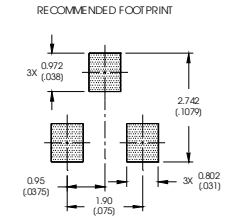
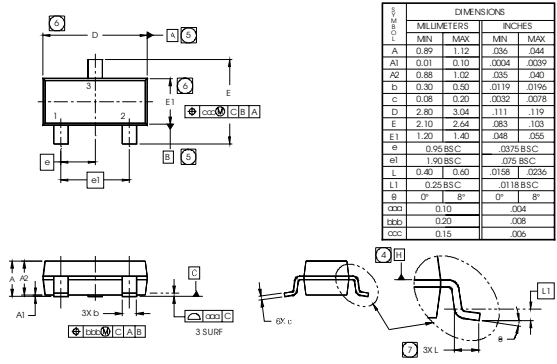
- NOTES:
 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
 2. CONTROLLING DIMENSION : INCH.
 ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.

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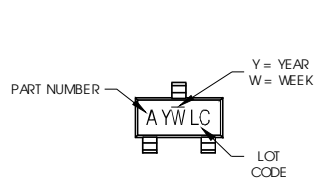
Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
 3. CONTROLLING DIMENSION: MILLIMETER.
 - ① DATUM PLANE B IS LOCATED AT THE MOLD PARTING LINE.
 - ② DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
 - ③ DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
 - ④ DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
 - ⑤ OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information



- PART NUMBER CODE REFERENCE:
- A = IRLML2402
 - B = IRLML2803
 - C = IRLML6302
 - D = IRLML5103
 - E = IRLML6402
 - F = IRLML6401
 - G = IRLML2502
 - H = IRLML5203

Note: A line above the work week (as shown here) indicates Lead-Free.

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

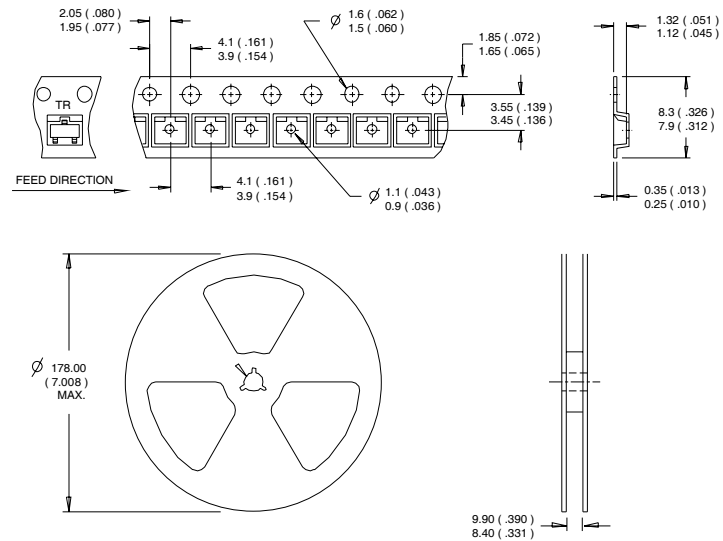
| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | 1 | 01 | A |
| 2002 | 2 | 02 | B |
| 2003 | 3 | 03 | C |
| 1994 | 4 | 04 | D |
| 1995 | 5 | | |
| 1996 | 6 | | |
| 1997 | 7 | | |
| 1998 | 8 | | |
| 1999 | 9 | | |
| 2000 | 0 | 24 | X |
| | | 25 | Y |
| | | 26 | Z |

W = (27-52) IF PRECEDED BY A LETTER

| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | A | 27 | A |
| 2002 | B | 28 | B |
| 2003 | C | 29 | C |
| 1994 | D | 30 | D |
| 1995 | E | | |
| 1996 | F | | |
| 1997 | G | | |
| 1998 | H | | |
| 1999 | J | | |
| 2000 | K | 50 | X |
| | | 51 | Y |
| | | 52 | Z |

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

International
IR Rectifier

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 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 11/04